

POST-FILM-FORMATION PROCESSING METHOD AND SUBSTRATE PROCESSING APPARATUS

ABSTRACT

Occurrence of metal contamination and adhesion of particles with respect to a zirconium film formed on a substrate is suppressed. A post-film-formation processing method of performing processing on a chamber having a processing space into which a processing gas containing zirconium chloride is supplied in a state where a substrate is accommodated in the processing space and in which a film formation process of forming a film formed of zirconium on the substrate is performed, at least a portion of the chamber exposed to the processing space being formed of a material containing aluminum, the method including: a processing gas discharge process of stopping supply of the processing gas after the film formation process and discharging the processing gas from the processing space; and a hydrogen nitride-based gas supply process of supplying a hydrogen nitride-based gas into the processing space after the processing gas discharge process.

(Fig. 6A)